

Figure 1.

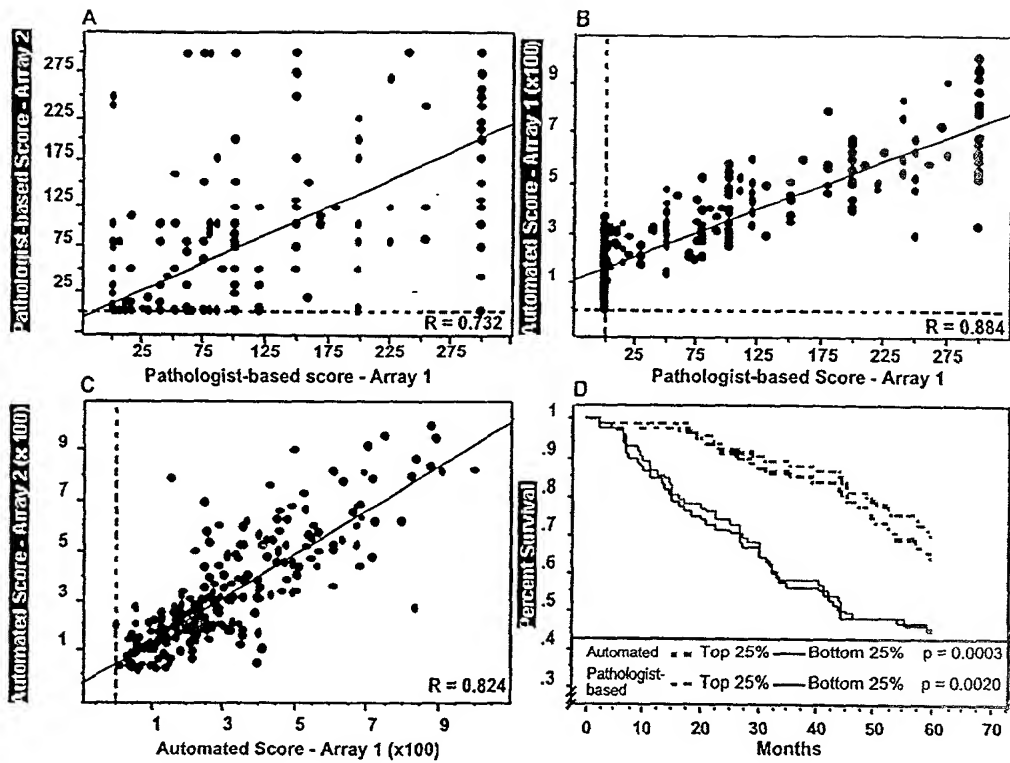


Figure 2

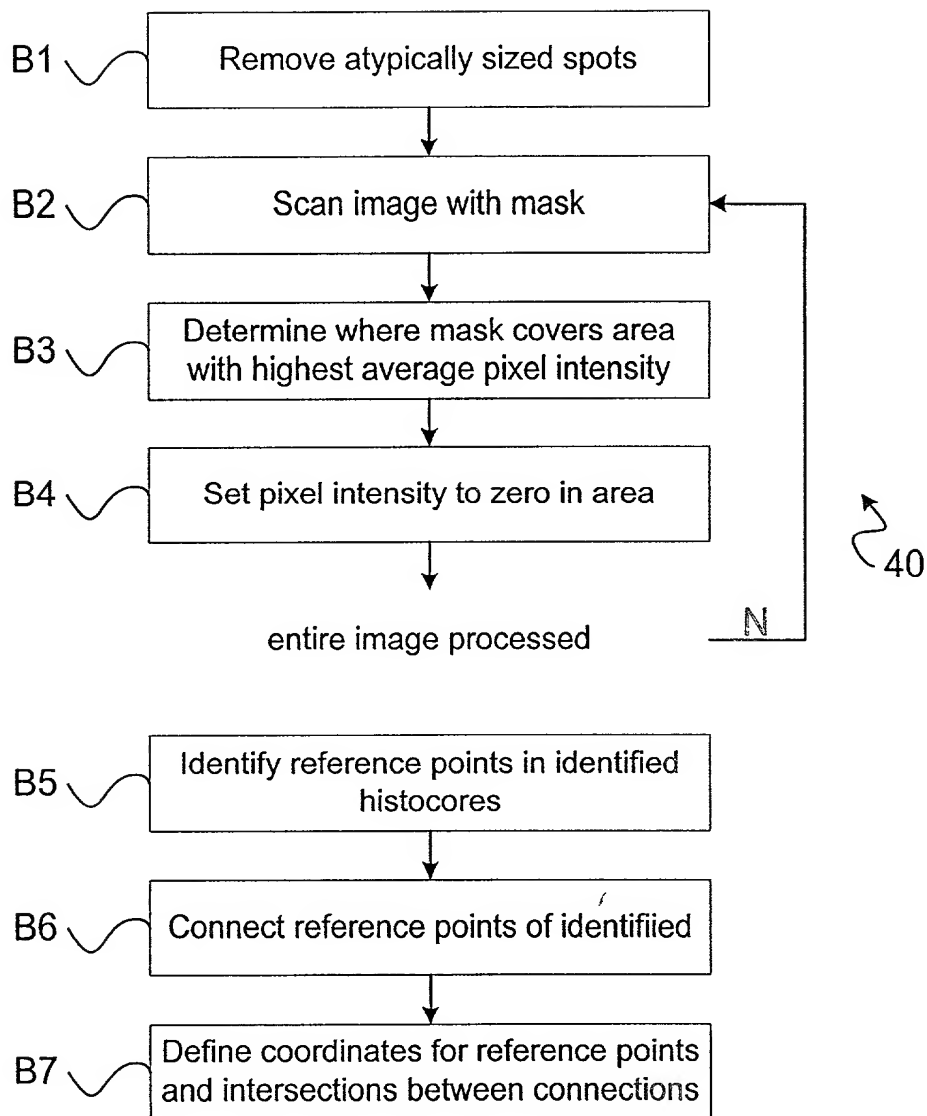


FIG. 3

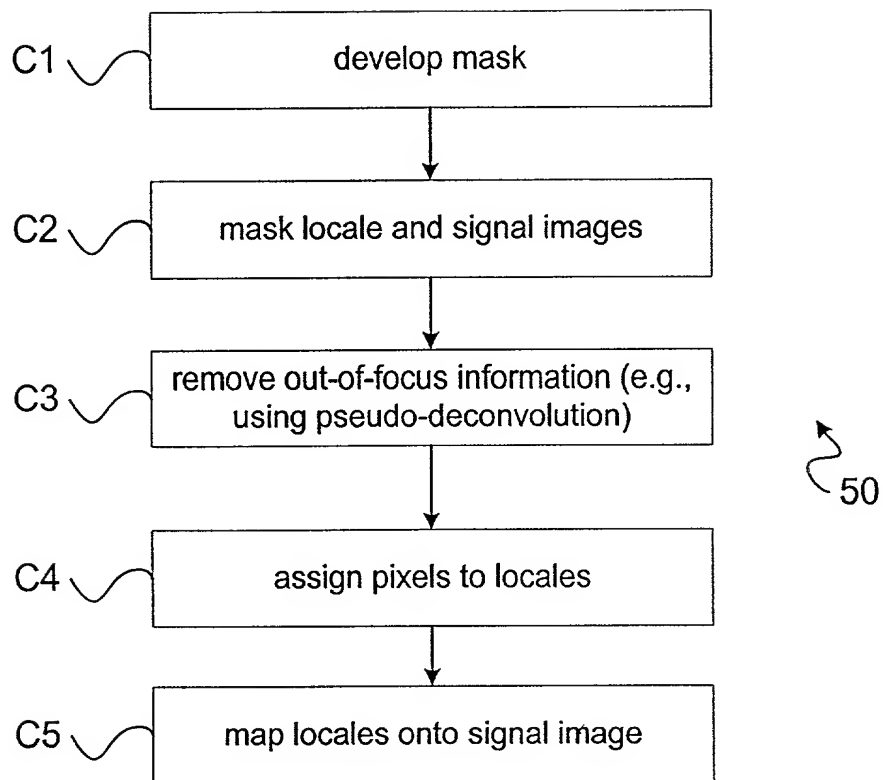


FIG. 4

100
↳

FIG. 5 is a schematic diagram of a device 100. The device 100 includes a substrate 110, a first layer 120, and a second layer 130. The first layer 120 is disposed on the substrate 110 and includes a grid of openings 120. The second layer 130 is disposed on the first layer 120 and includes a grid of openings 130. The openings 120 and 130 are arranged in a staggered pattern.

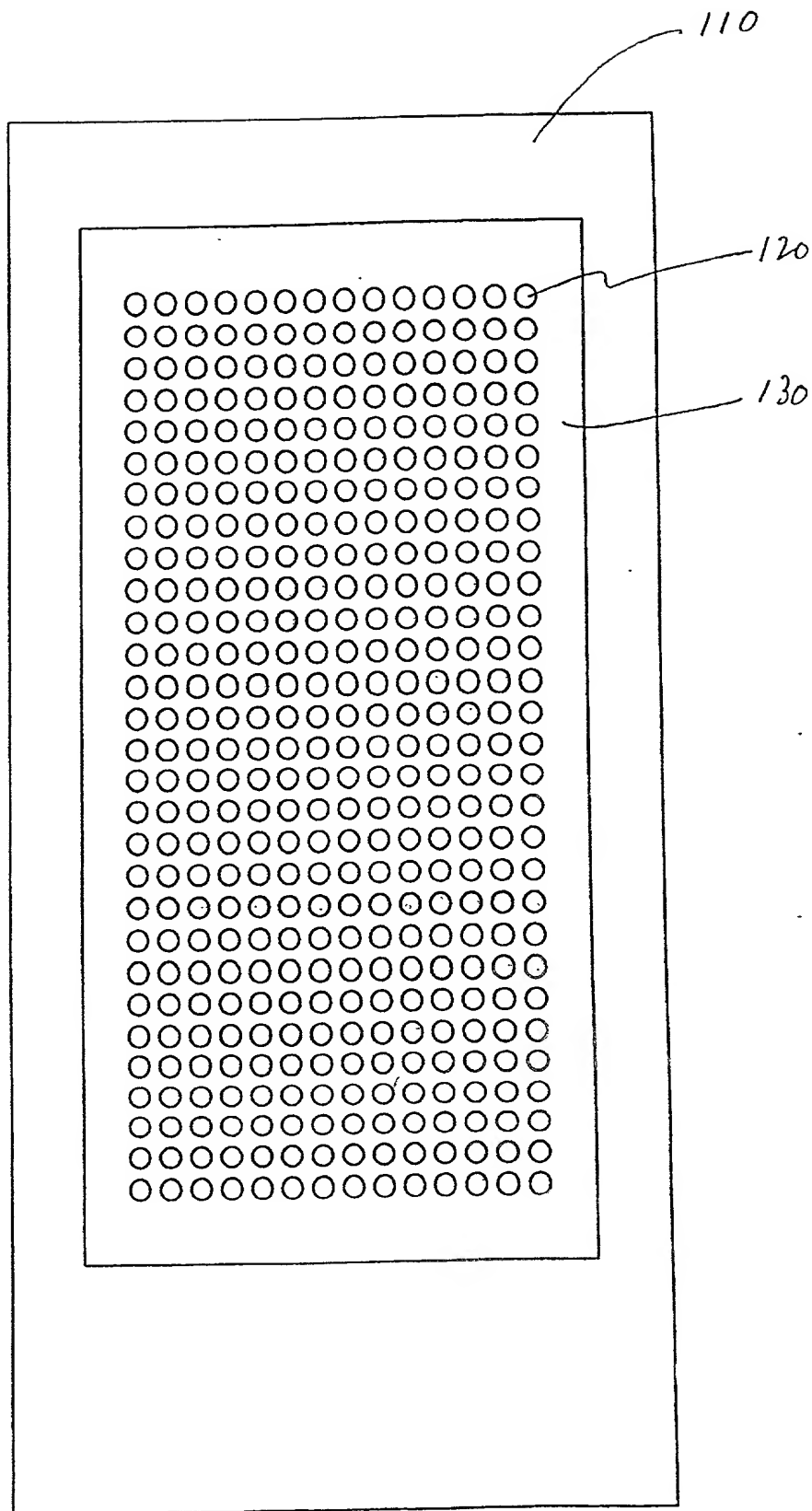


FIG. 5

FIG. 6 is a schematic diagram of a system 200 for processing a substrate 100. The system 200 includes a substrate 100, a processing chamber 210, a gas inlet 220, a gas outlet 230, a temperature sensor 240, a pressure sensor 250, and a control system 260. The control system 260 is connected to the processing chamber 210 and the gas inlet 220. The processing chamber 210 is connected to the gas inlet 220 and the gas outlet 230. The temperature sensor 240 is located inside the processing chamber 210. The pressure sensor 250 is located outside the processing chamber 210. The control system 260 is connected to the temperature sensor 240 and the pressure sensor 250.

200
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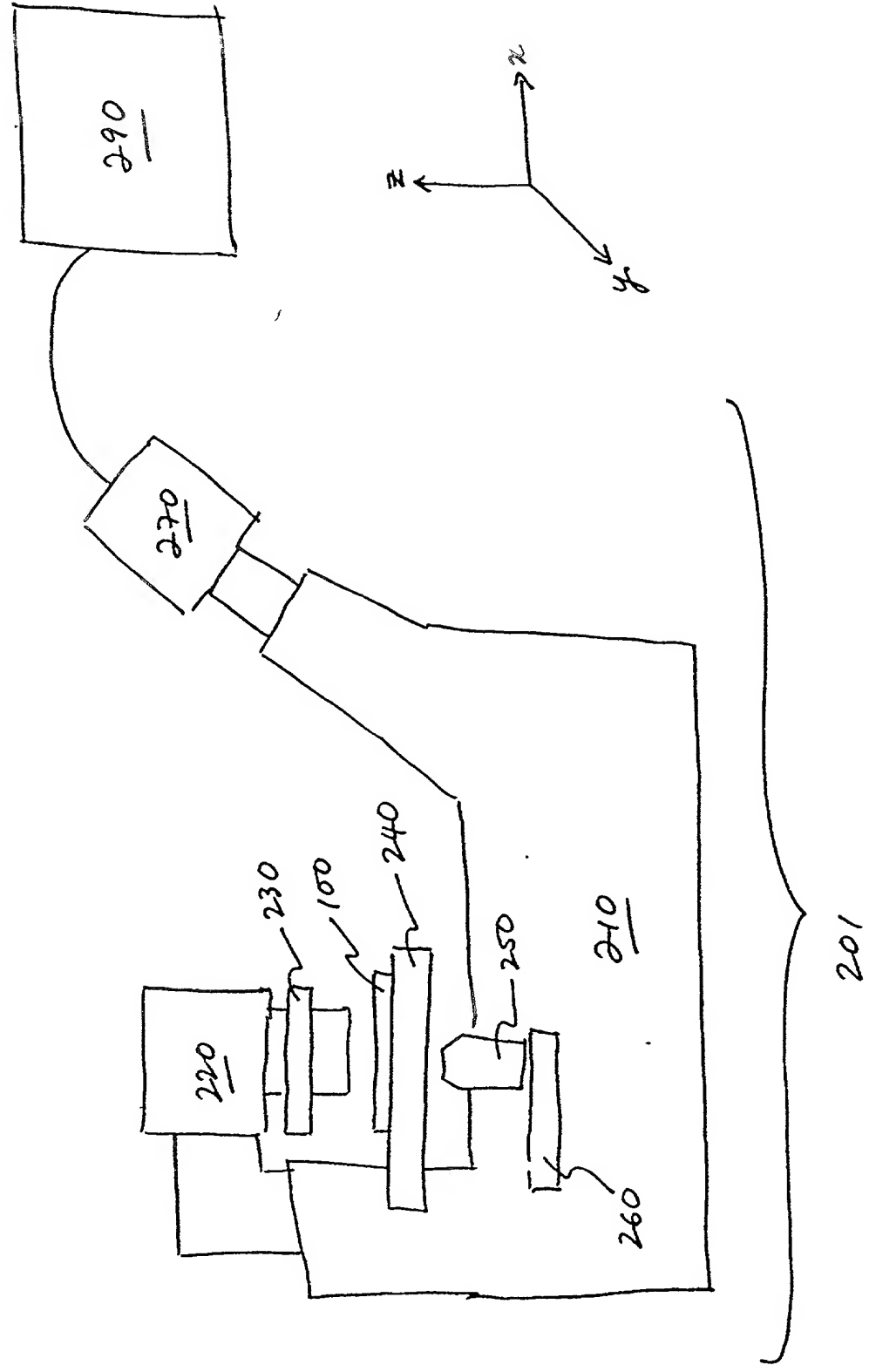


FIG. 6